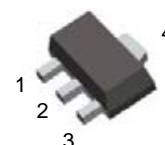


PNPSURFACEMOUNTTRANSISTOR

- We declare that the material of product compliance with RoHS requirements.

L2SB882Q
L2SB882P



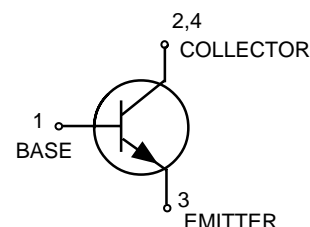
SOT-89

DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
L2SB882Q	82Q	2500/Tape&Reel
L2SB882P	82P	2500/Tape&Reel

MAXIMUM RATINGS(Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CB0}	40	V
Collector-emitter voltage	V _{CEO}	30	V
Emitter-base voltage	V _{EBO}	6	V
Peak Pulse Current	I _{CM}	3	A
Collector power dissipation	P _c	0.5	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to 150	°C



ELECTRICAL CHARACTERISTICS(Ta=25°C)

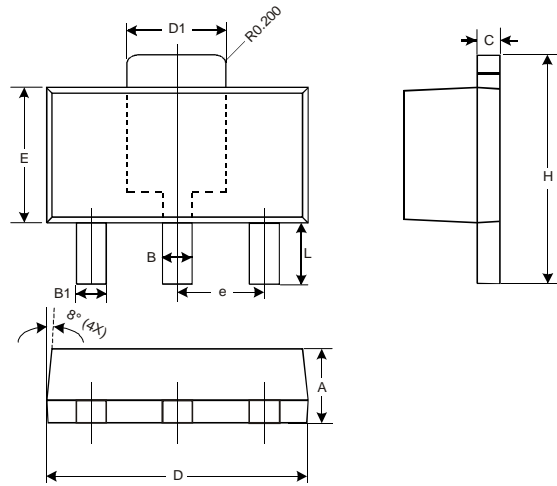
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CB0}	40	-	-	V	I _c = 100μA
Collector-emitter breakdown voltage	BV _{CEO}	30	-	-	V	I _c = 10mA
Emitter-base breakdown voltage	BV _{EBO}	6	-	-	V	I _E = 100μA
Collector cutoff current	I _{CB0}	-	-	1	μA	V _{CB} = 40V
Collector cutoff current	I _{CEO}	-	-	10	μA	V _{CB} = 30V
Emitter cutoff current	I _{EBO}	-	-	1	μA	V _{EB} = 6V
Collector-emitter saturation voltage	V _{CE(sat)}	-	-	0.5	V	I _c /I _B =2A/0.2A
Base-emitter saturation voltage	V _{BE(sat)}	-	-	1.5	V	I _c /I _B =2A/0.2A
DC current transfer ratio	h _{FE(1)}	100	-	320	-	V _{CE} =2V, I _c =1A
DC current transfer ratio	h _{FE}	32	-	-	-	V _{CE} =2V, I _c =100mA
Transition frequency	f _t	50	-	-	MHz	V _{CE} =5V, I _E =0.1A, f=10MHz

h_{FE(1)} values are classified as follows :

Item(*)	Q	P
h _{FE}	100~200	160~320

SOT-89

Unit: mm



SOT89-3L			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.45	0.55	0.50
B1	0.37	0.47	0.42
C	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.50	1.70	1.60
E	2.40	2.60	2.50
e	—	—	1.50
H	3.95	4.25	4.10
L	0.90	1.20	1.05
All Dimensions in mm			

